

**AMENDMENTS TO THE CLAIMS**

Please **AMEND** claim 45, as shown below.

Please **ADD** claims 51-54 as shown below.

The following is a complete list of all claims in this application.

1-9. (Cancelled)

10. (Previously Presented) A contact structure of a wire, comprising:

a wire of a conductive material on a substrate;

an inter-layer reaction layer formed on the wire and including at least silicon or transition metal; and

a conductive layer electrically connected to the wire via the inter-reaction layer.

11. (Original) The contact structure of claim 10, wherein the wire is made of a conductive material including aluminum-based material.

12. (Original) The contact structure of claim 11, wherein the inter-layer reaction layer includes at least  $\text{Al}_x\text{Si}_x$ .

13. (Original) The contact structure of claim 10, wherein the inter-layer reaction layer is inter-metallic compound layer.

14. (Original) The contact structure of claim 10, wherein the conductive layer is made of a transparent conductive material of indium zinc oxide.

15. (Original) The contact structure of claim 10, further comprising an insulating layer having a contact hole exposing the inter-layer reaction layer between the wire and the conductive layer.

16-44. (Cancelled)

45. (Currently Amended) A thin film transistor array panel, comprising:  
a gate wire made of a first conductive material on an insulating substrate;  
a gate insulating layer covering the gate wire;  
a semiconductor layer formed on the gate insulating layer;  
a data wire made of a second conductive material on the gate insulating layer and the semiconductor layer;  
a passivation layer covering the data wire;  
an inter-layer reaction layer formed on the gate wire and the data wire; and  
a transparent conductive layer pattern electrically connected to the gate wire or the data wire through a first contact hole of the gate insulating layer or the passivation layer via the first contact hole,  
wherein the transparent conductive pattern is electrically connected to the gate wire or the data wire via the inter-layer reaction layer.

46. (Original) The thin film transistor array panel of claim 45, wherein the first and the second conductive material include a metal of aluminum-based material.

47. (Original) The thin film transistor array panel of claim 45, wherein the insulating layer and the passivation layer are made of silicon-nitride.

48. (Original) The thin film transistor array panel of claim 45, wherein the transparent conductive layer pattern is made of indium zinc oxide.

49. (Original) The thin film transistor array panel of claim 45, wherein the gate wire includes a gate line, a gate electrode connected to the gate line, and a gate pad which is connected to the gate line and receives a signal from an external circuit, and the data wire includes a data line, a source electrode connected to the data line, a drain electrode which is separated from the drain electrode and opposite to the drain electrode with the respect to the gate electrode, and a data pad which is connected to the data line and receives a signal from an external circuit.

50. (Original) The thin film transistor array panel of claim 45, wherein the inter-layer reaction layer includes silicon or transition metal.

51. (New) A wiring contact structure, comprising:  
a first wire formed of a conductive material; and

a second wire formed on and in contact with the first wire, the second wire comprising:  
a first conductive layer formed of a conductive material; and  
a second conductive layer sandwiched between the first wire and the first  
conductive layer and containing silicon or transition metal,  
wherein the first conductive layer is electrically connected to the first wire via the second  
conductive layer.

52. (New) The wiring contact structure of claim 51, wherein the first wire contains  
aluminum.

53. (New) The wiring contact structure of claim 52, wherein the second conductive  
layer contains  $\text{Al}_x\text{Si}_x$ .

54. (New) The wiring contact structure of claim 51, wherein the first conductive layer  
is formed of a transparent conductive material.